MOSFETs Silicon N-Channel MOS (DTMOSIV)

TK62N60W

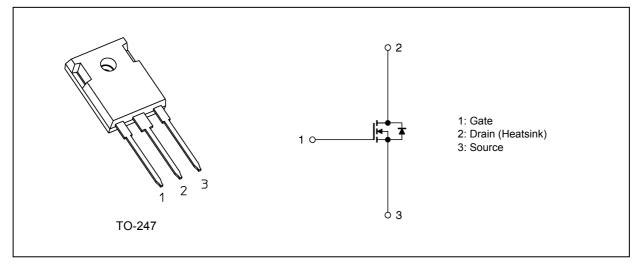
1. Applications

Switching Voltage Regulators

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)} = 0.033 \Omega$ (typ.) by used to Super Junction Structure : DTMOS
- (2) Easy to control Gate switching
- (3) Enhancement mode: V_{th} = 2.7 to 3.7 V ($V_{\rm DS}$ = 10 V, $I_{\rm D}$ = 3.1 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Rating	Unit	
Drain-source voltage		V _{DSS}	600	V
Gate-source voltage		V _{GSS}	±30	7
Drain current (DC)	(Note 1)	Ι _D	61.8	A
Drain current (pulsed)	(Note 1)	I _{DP}	247	
Power dissipation (T _c =	= 25°C)	PD	400	W
Single-pulse avalanche energy	(Note 2)	E _{AS}	698	mJ
Avalanche current		I _{AR}	15.5	Α
Reverse drain current (DC)	(Note 1)	I _{DR}	61.8	
Reverse drain current (pulsed)	(Note 1)	I _{DRP}	247	
Channel temperature		T _{ch}	150	°C
Storage temperature		T _{stg}	-55 to 150	7
Mounting torque		TOR	0.8	N · m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production 2012-09

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R _{th(ch-c)}	0.313	°C/W
Channel-to-ambient thermal resistance	R _{th(ch-a)}	50	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_DD = 90 V, T_ch = 25°C (initial), L = 5.08 mH, R_G = 25 Ω , I_AR = 15.5 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

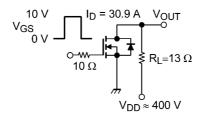
6. Electrical Characteristics

6.1. Static Characteristics (Ta = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{GS} = ±30 V, V_{DS} = 0 V	_	_	±1	μA
Drain cut-off current	I _{DSS}	V _{DS} = 600 V, V _{GS} = 0 V	_	_	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	600	—	—	V
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 3.1 mA	2.7	_	3.7	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 30.9 A		0.033	0.040	Ω

6.2. Dynamic Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 300 V, V _{GS} = 0 V, f = 100 kHz	_	6500	_	pF
Reverse transfer capacitance	C _{rss}]	_	20	_	
Output capacitance	C _{oss}		_	140	_	
Effective output capacitance	C _{o(er)}	V_{DS} = 0 to 400 V, V_{GS} = 0 V	_	200	_	
Gate resistance	r _g	V _{DS} = OPEN, f = 1 MHz	_	2	_	Ω
Switching time (rise time)	t _r	See Figure 6.2.1	_	58	_	ns
Switching time (turn-on time)	t _{on}]	_	115	_	
Switching time (fall time)	t _f]	_	15	_	
Switching time (turn-off time)	t _{off}]	_	310		
MOSFET dv/dt ruggedness	dv/dt	V _{DD} = 0 to 400 V, I _D = 15.5 A	50	_	_	V/ns



Duty \leq 1%, $t_W =$ 10 μs

Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 400 \text{ V}, V_{GS} \text{ = } 10 \text{V}, \text{I}_{D} \text{ = } 61.8 \text{A}$	_	180	—	nC
Gate-source charge 1	Q _{gs1}		_	38	_	
Gate-drain charge	Q _{gd}		_	85	_	

6.4. Source-Drain Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V _{DSF}	I _{DR} = 61.8 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	I _{DR} = 30.9 A, V _{GS} = 0 V	_	500	_	ns
Reverse recovery charge	Q _{rr}	-dI _{DR} /dt = 50 A/μs	_	7	_	μC
Peak reverse recovery current	I _{rr}		_	25	_	А
Diode dv/dt ruggedness	dv/dt	I_{DR} = 30.9 A, V_{GS} = 0 V, V_{DD} = 400 V	15	_	_	V/ns

TK62N60W

7. Marking (Note)

TOSHIBA

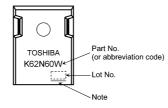


Fig. 7.1 Marking

 Note:
 A line under a Lot No. identifies the indication of product Labels.

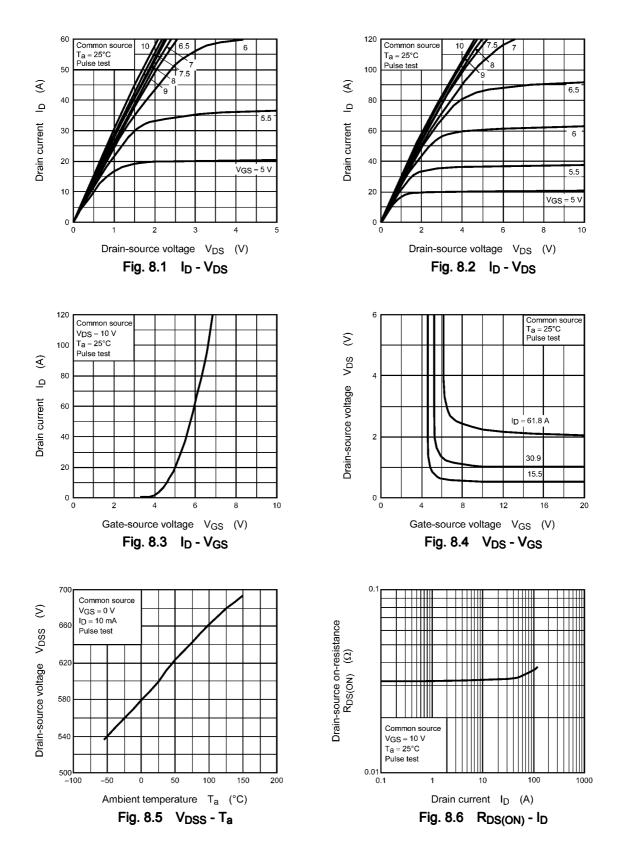
 Not underlined: [[Pb]]/INCLUDES > MCV

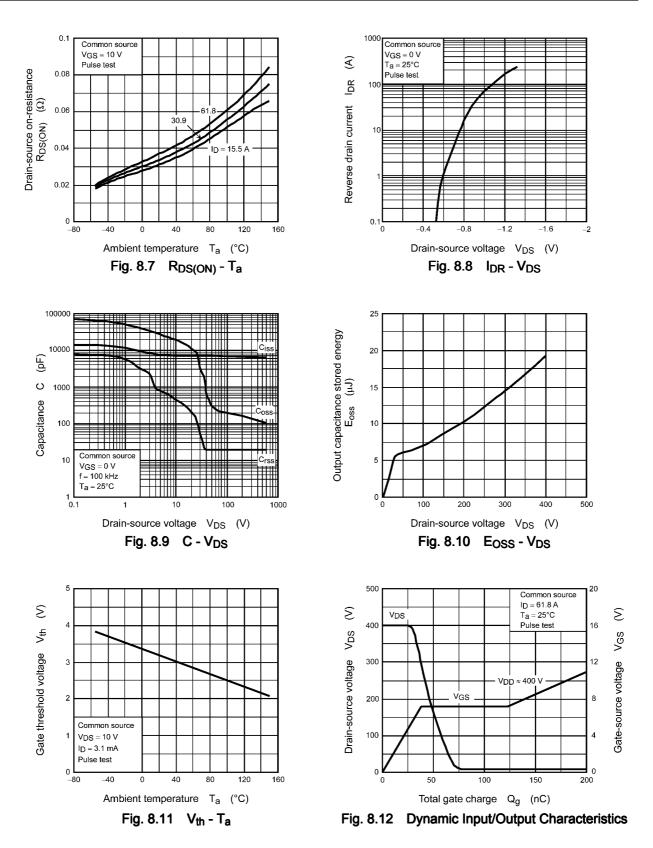
 Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

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 The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

8. Characteristics Curves (Note)





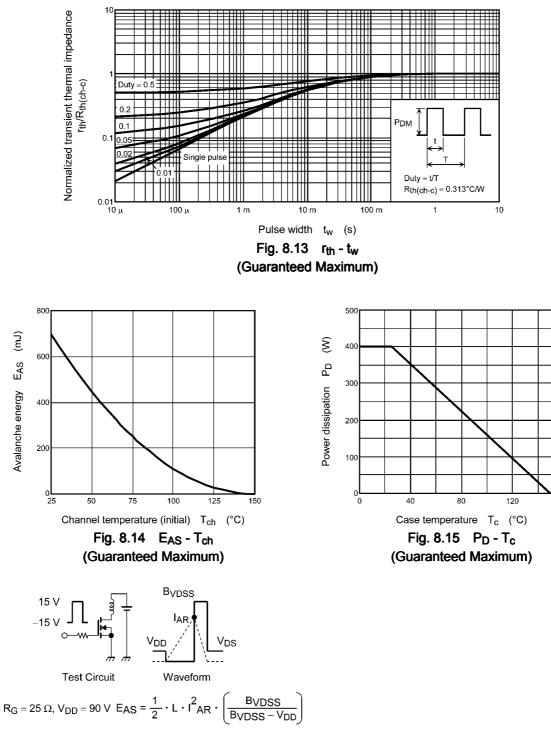
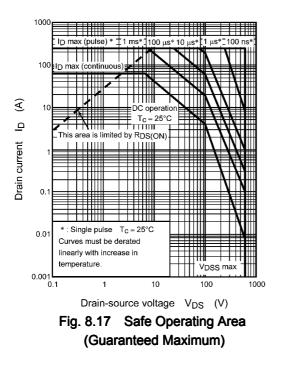


Fig. 8.16 Test Circuit/Waveform

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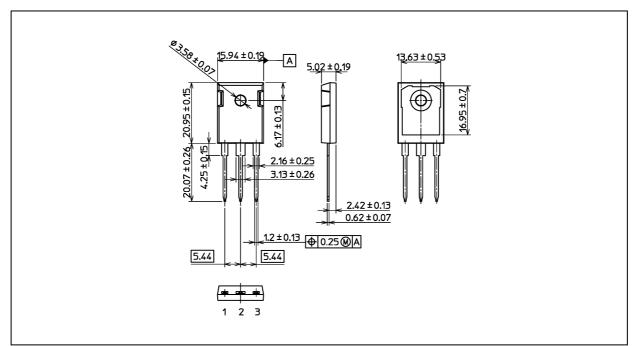


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 6.15 g (typ.)

Package Name(s)			
JEITA: SC-65			
TOSHIBA: 2-16L1A			
Nickname: TO-247			

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